

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization  
International Bureau



(43) International Publication Date  
8 November 2001 (08.11.2001)

PCT

(10) International Publication Number  
WO 01/83395 A1

(51) International Patent Classification<sup>7</sup>: C04B 35/46,  
H01B 3/12

[KR/KR]; Taeneung-woosung Apt. 6-803, Kongneung  
2-dong, Nowon-ku, Seoul 139-242 (KR). KIM, Hyo-Tae  
[KR/KR]; Kist Dormitory 36, 39-1, Hawolgok-dong,  
Sungbook-ku, Seoul 136-791 (KR).

(21) International Application Number: PCT/KR00/00984

(74) Agent: PARK, Jang-Won; Jewoo Building 5th floor, 200,  
Nonhyun-dong, Kangnam-ku, Seoul 135-010 (KR).

(22) International Filing Date: 30 August 2000 (30.08.2000)

(81) Designated States (national): CN, IN, JP, US.

(25) Filing Language: Korean

(84) Designated States (regional): European patent (AT, BE,  
CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC,  
NL, PT, SE).

(26) Publication Language: English

Published:

— with international search report

(30) Priority Data:

2000-23676 3 May 2000 (03.05.2000) KR

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

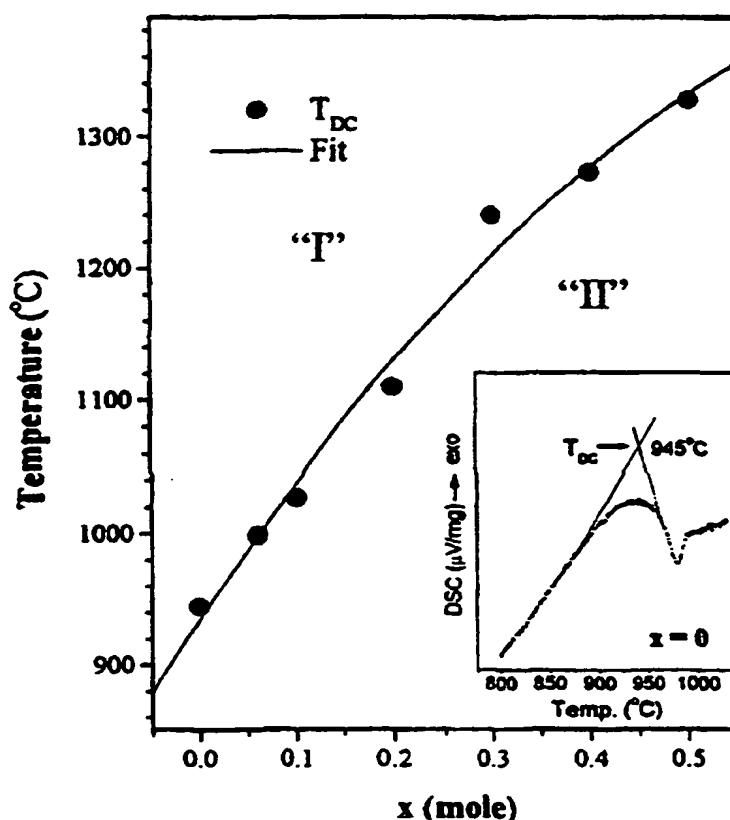
(71) Applicant (for all designated States except US): KOREA  
INSTITUTE OF SCIENCE AND TECHNOLOGY

[KR/KR]; 39-1, Hawolgok-dong, Sungbook-ku, Seoul  
136-791 (KR).

(72) Inventors; and

(75) Inventors/Applicants (for US only): KIM, Yoon-Ho

(54) Title: LOW TEMPERATURE SINTERABLE AND LOW LOSS DIELECTRIC CERAMIC COMPOSITIONS AND  
METHOD THEREOF



(57) Abstract: A low loss high-frequency dielectric ceramic composition for sintering at a low temperature and method of manufacturing the same which is characterized in that excellent dielectric properties such as a much lower sintering temperature and higher quality coefficient and dielectric constant, compared to a conventional high-frequency ceramic composition, a stabilized temperature coefficient, and a temperature compensating property varied according to a composition, are implemented using a low-priced material such as ZnO-Mo (M=Mg, Co, Ni)-TiO<sub>2</sub>. In addition, Ag, Cu, an alloy thereof, or an Ag/Pd alloy can be used as an internal electrode. Thus, the composition of the present invention can be used as a dielectric material for all sorts of high-frequency devices, such as a multilayer chip capacitor, multilayer chip filter, multilayer chip capacitor/inductor composite device and module, low temperature sintered substrate, resonator or filter and ceramic antenna.

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